

Description

The AP2161D and AP2171D are integrated high-side power switches optimized for Universal Serial Bus (USB) and other hot-swap applications. The family of devices complies with USB 2.0 and is available with both polarities of Enable input. They offer current and thermal limiting and short circuit protection as well as controlled rise time and under-voltage lockout functionality. A 7ms deglitch capability on the opendrain Flag output prevents false over-current reporting and does not require any external components.

All devices are available in SOT25, SO-8, MSOP-8EP, and U-DFN2018-6 packages.

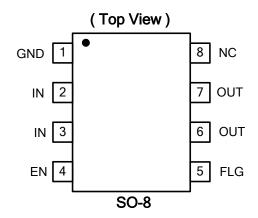
Features

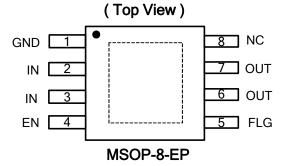
- · Single USB port power switches with output discharge
- Over-current and thermal protection
- 1.5A accurate current limiting
- Fast transient response
- · Reverse Current Blocking
- 90mΩ on-resistance
- Input voltage range: 2.7V 5.5V
- 0.6ms typical rise time
- Very low shutdown current: 1uA (max)
- Fault report (FLG) with blanking time (7ms typ)
- ESD protection: 4KV HBM, 300V MM
- Active high (AP2171D) or active low (AP2161D) enable
- Ambient temperature range -40°C to 85℃
- SOT25, SO-8, MSOP-8EP (Exposed Pad), and U-DFN2018-6: Available in "Green" Molding Compound (No Br, Sb)
- Lead Free Finish / RoHS Compliant (Note 1)
- UL Recognized, File Number E322375
- IEC60950-1 CB Scheme Certified

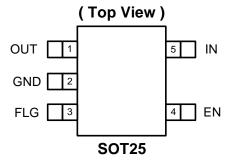
Applications

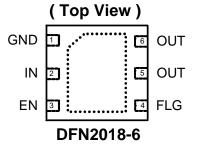
- Consumer electronics LCD TV & Monitor, Game Machines
- Communications Set-Top-Box, GPS, Smartphone
- Computing Laptop, Desktop, Servers, Printers, Docking Station, HUB

Pin Assignments





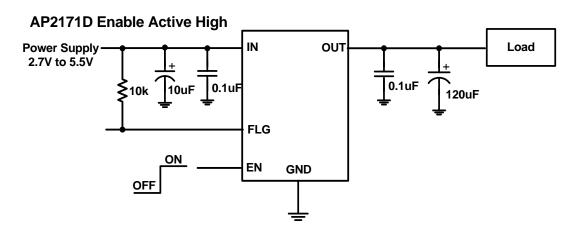




Notes: 1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied. Please visit our website at http://www.diodes.com/products/lead_free.html.



Typical Application Circuit



Available Options

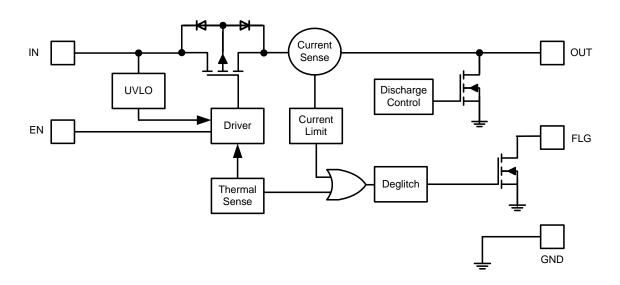
Part Number	Channel	Enable pin (EN)	Current limit (typical)	Recommended maximum continuous load current
AP2161D	1	Active Low	1.5A	1A
AP2171D	1	Active High	1.5A	1A

Pin Descriptions

D:	Pin Number			
Pin Name	SO-8	SOT25	U-DFN2018-6	Descriptions
Name	MSOP-8EP	30123	O-DFN2010-0	
GND	1	2	1	Ground
IN	2, 3	5	2	Voltage input pin (all IN pins must be tied together externally)
EN	4	4	3	Enable input, active low (AP2161D) or active high (AP2171D)
FLG	5	3	4	Over-current and over-temperature fault report; open-drain flag is active low when triggered
OUT	6, 7	1	5, 6	Voltage output pin (all OUT pins must be tied together externally)
NC	8	N/A	N/A	No internal connection; recommend tie to OUT pins



Functional Block Diagram



Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
ESD HBM	Human Body Model ESD Protection	4	KV
ESD MM	Machine Model ESD Protection	300	V
V_{IN}	Input Voltage	6.5	V
V _{OUT}	Output Voltage	V _{IN} + 0.3	V
V_{EN} , V_{FLG}	Enable Voltage	6.5	V
I _{load}	Maximum Continuous Load Current	Internal Limited	A
T _{Jmax}	Maximum Junction Temperature	150	C
T _{ST}	Storage Temperature Range (Note 2)	-65 to 150	\mathcal{C}

Notes: 2. UL Recognized Rating from -30℃ to 70℃ (Diodes qualified T _{ST} from -65℃ to 150℃)

Recommended Operating Conditions

Symbol	Parameter	Min	Max	Unit
V _{IN}	Input voltage	2.7	5.5	V
l _{out}	Output Current	0	1.0	А
T _A	Operating Ambient Temperature	-40	85	°C



Electrical Characteristics (T_A = 25°C, V_{IN} = +5.0V, unless otherwise stated)

Symbol	Parameter		Test Cor	nditions	Min	Тур.	Max	Unit
V _{UVLO}	Input UVLO				1.6	1.9	2.5	V
I _{SHDN}	Input Shutdown Current	Disabled, I _{OUT} = 0			0.5	1	μΑ	
IQ	Input Quiescent Current	Enabled, I _{OUT}	= 0			45	70	μΑ
I _{LEAK}	Input Leakage Current	Disabled, OU	T grounded			0.1	1	μΑ
I _{REV}	Reverse Leakage Current	Disabled, V _{IN}	= 0V, V _{OUT} =	5V, I _{REV} at V _{IN}		0.1	1	μΑ
		V _{IN} = 5V,	T _A = 25°C	SOT25, MSOP-8-EP, SO-8		95	115	
R _{DS(ON)}	Switch on-resistance	I _{OUT} = 1A		DFN2018-6		90	110	
()			-40°C ≤ T _A	≤ 85°C			140	mΩ
		$V_{IN} = 3.3V,$	T _A = 25°C			120	140	
		I _{OUT} = 1A	-40°C ≤ T _A	≤ 85°C			170	
I _{SHORT}	Short-Circuit Current Limit	Enabled into	short circuit,	C _L =22μF		1.2		Α
I _{LIMIT}	Over-Load Current Limit	V _{IN} = 5V, V _{OUT} = 4.0V, C _L =120μF,-40°C ≤ T _A ≤85°C		1.1	1.5	1.9	Α	
I _{Trig}	Current limiting trigger threshold	Output Current Slew rate (<100A/s) , C _L =22μF			2.0		Α	
V_{IL}	EN Input Logic Low Voltage	V _{IN} = 2.7V to 5.5V				0.8	V	
V _{IH}	EN Input Logic High Voltage	V _{IN} = 2.7V to 5.5V		2			V	
I _{SINK}	EN Input leakage	V _{EN} = 5V				1	μА	
T _{D(ON)}	Output turn-on delay time	$C_L=1\mu F, R_{load}=10\Omega$			0.05		ms	
T _R	Output turn-on rise time	$C_L=1\mu F$, $R_{load}=10\Omega$			0.6	1.5	ms	
T _{D(OFF)}	Output turn-off delay time	$C_L=1\mu F$, $R_{load}=10\Omega$			0.05		ms	
T _F	Output turn-off fall time	$C_L=1\mu F, R_{load}=10\Omega$			0.05	0.1	ms	
R_{FLG}	FLG output FET on-resistance	I _{FLG} =10mA				20	40	Ω
T _{Blank}	FLG blanking time	C _{IN} =10uF, C _L	=22μF		4	7	15	ms
R _{DIS}	Discharge resistance (Note 3)	V _{IN} = 5V, disabled, I _{OUT} = 1mA			100		Ω	
T _{DIS}	Discharge Time	CL= 1µF, VIN = 5V, disabled to VOUT < 0.5V			0.6		ms	
T _{SHDN}	Thermal Shutdown Threshold	Enabled, R _{load} =1kΩ			140		°C	
T _{HYS}	Thermal Shutdown Hysteresis				25		°C	
		SOT25 (Note	4)			170		
•	Thermal Resistance Junction-to-	SO-8 (Note 4	·)			127		00.044
θ_{JA}	Ambient	MSOP-8EP (Note 5)			67		°C/W
		U-DFN2018-	6 (Note 5)			70		

Notes:

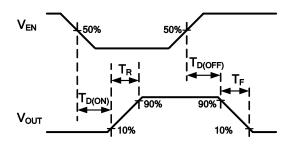
- 3. The discharge function is active when the device is disabled (when enable is de-asserted). The discharge function offers a resistive discharge path for the external storage capacitor.
- Device mounted on FR-4 4 substrate PCB, 2oz copper, with minimum recommended pad layout.
 Device mounted on 2" x 2" FR-4 substrate PCB, 2oz copper, with minimum recommended pad on top layer and thermal vias to bottom layer ground

2V/div



1A SINGLE CHANNEL CURRENT-LIMITED POWER SWITCH WITH OUTPUT DISCHARGE

Typical Performance Characteristics



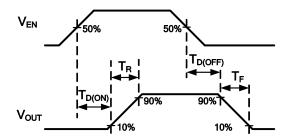


Figure 1. Voltage Waveforms: AP2161D (left), AP2171D (right)

All Enable Plots are for AP2171D Active High

Turn-On Delay and Rise Time

Turn-Off Delay and Fall Time

5V/div Ven Vout 2V/div C_L=1uF T_A=25℃ C_L=1uF $R_L=10\Omega$ T_A=25℃ RL=10Ω

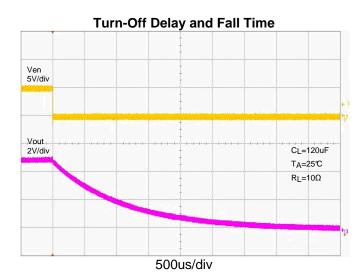
> 100us/div 100us/div

> > C_L=120uF

TA=25℃ $R_L=10\Omega$

Turn-On Delay and Rise Time

Ven 5V/div Vout 2V/div



500us/div



AP2161D/AP2171D

1A SINGLE CHANNEL CURRENT-LIMITED POWER SWITCH WITH OUTPUT DISCHARGE

Typical Performance Characteristics (Continued)

Short Circuit Current, Device Enabled Into Short

Short Circuit with Blanking Time and Recovery

Vout 5V/div

Vflag 2V/div

Ven 5V/div

V_{IN}=5V

T_A=25℃ C_L=22uF

lout 500mA/div lout

V_{IN}=5V T_A=25℃ C_L=22uF

100us/div

20ms/div

1 Ω Load Connected to Enabled Device

2 Ω Load Connected to Enabled Device

Vflag 2V/div

V_{IN}=5V T_A=25℃ C_L=22uF Vflag 2V/div V_{IN}=5V T_A=25℃ C_L=22uF

lout 1A/div

1ms/div

lout 1A/div

1ms/div

Power On

 T_A =25℃ C_L =120uF R_L =10Ω

Vflag

Vflag 5V/div

lout 500mA/div T_A =25℃ C_L =120uF R_L =10Ω

lout 500mA/div

Ven 5V/div

Ven 5V/div

Vout 5V/div Vout 5V/div

2ms/div

20ms/div

Power Off



Typical Performance Characteristics (Continued)

UVLO Increasing UVLO Decreasing

 $T_A=25^{\circ}C$ $C_L=22uF$ $R_L=10\Omega$

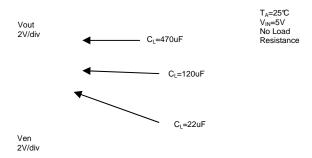
Vin 2V/div $T_A=25^{\circ}C$ $C_L=22uF$ $R_L=10\Omega$

Vin 2V/div

lout 500mA/div lout 500mA/div

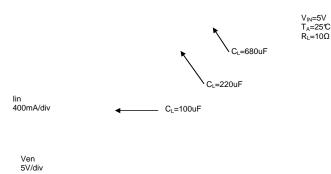
2ms/div

Discharge Time No Load Resistance

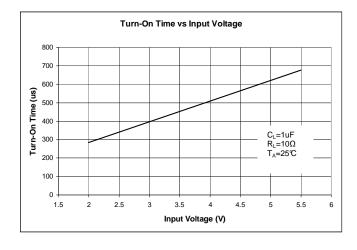


20ms/div

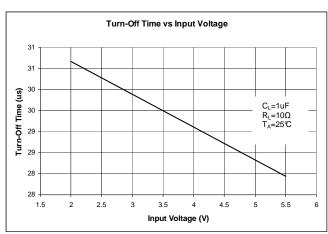
Inrush Current



100ms/div

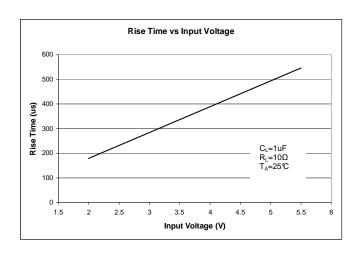


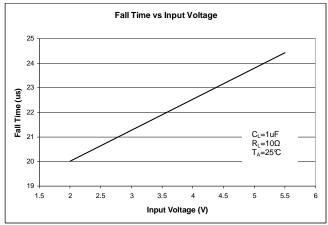
1ms/div

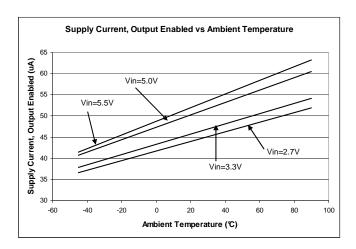


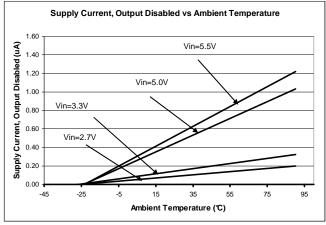


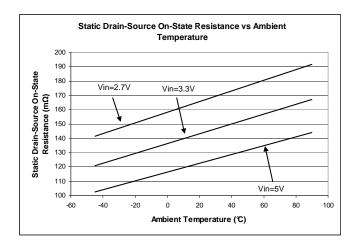
Typical Performance Characteristics (Continued)

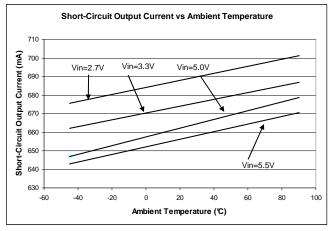






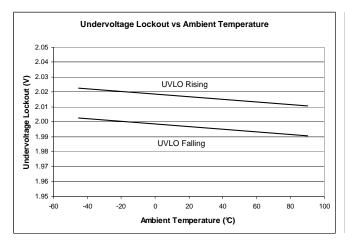


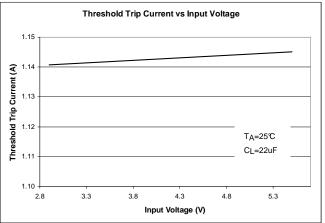






Typical Performance Characteristics (Continued)







Application Note

The AP2161D and AP2171D are integrated high-side power switches optimized for Universal Serial Bus (USB) that require protection functions. The power switches are equipped with a driver that controls the gate voltage and incorporates slew-rate limitation. This, along with the various protection features and special functions, makes these power switches ideal for hot-swap or hot-plug applications.

Protection Features:

Under-voltage Lockout (UVLO)

Under-voltage lockout function (UVLO) guarantees that the internal power switch is initially off during start-up. The UVLO functions only when the switch is enabled. Even if the switch is enabled, the switch is not turned ON until the power supply has reached at least 1.9V. Whenever the input voltage falls below approximately

1.9V, the power switch is turned off. This facilitates the design of hot-insertion systems where it is not possible to turn off the power switch before input power is removed.

Over-current and Short Circuit Protection

An internal sensing FET is employed to check for overcurrent conditions. Unlike current-sense resistors, sense FETs do not increase the series resistance of the current path. When an over-current condition is detected, the device maintains a constant output current and reduces the output voltage accordingly. Complete shutdown occurs only if the fault stays long enough to activate thermal limiting.

The different overload conditions and the corresponding response of the AP2161D/2171D are outlined below:

S.NO	Conditions	Explanation	Behavior of the AP2161D/2171D
1	Short circuit condition at start-up	Output is shorted before input voltage is applied or before the part is enabled	The IC senses the short circuit and immediately clamps output current to a certain safe level namely I _{LIMIT} .
2	Short-circuit or over- current condition	Short-Circuit or Overload condition that occurs when the part is enabled.	 At the instance the overload occurs, higher current may flow for a very short period of time before the current limit function can react. After the current limit function has tripped (reached the over-current trip threshold), the device switches into current limiting mode and the current is clamped at I_{LIMIT}.
3	Gradual increase from nominal operating current to I _{LIMIT}	Load increases gradually until the current-limit threshold.(I _{TRIG})	The current rises until I _{TRIG} or thermal limit. Once the threshold has been reached, the device switches into its current limiting mode and is set at I _{LIMIT} .

Note that when the output has been shorted to GND at extremely low temperature (< -30°C), a minimum 120- μF electrolytic capacitor on the output pin is recommended. A correct capacitor type with capacitor voltage rating and temperature characteristics must be properly chosen so that capacitance value does not drop too low at the extremely low temperature operation. A recommended capacitor should have temperature characteristics of less than 10% variation of capacitance change when operated at extremely low temp. Our recommended aluminum electrolytic capacitor type is Panasonic FC series.

Thermal Protection

Thermal protection prevents the IC from damage when the die temperature exceeds safe margins. This mainly occurs when heavy-overload or short-circuit faults are present for extended periods of time. AP2161D/AP2171D implements thermal sensing to monitor the operating junction temperature of the power distribution switch. Once the die temperature rises to approximately 140°C, the Therma I protection feature gets activated as follows: The internal thermal sense circuitry turns the power switch off and the FLG output is asserted thus preventing the power switch from damage. Hysteresis in the thermal sense circuit allows the device to cool down to approximately 25℃ before the output is turned back on. The built-in thermal hysteresis feature avoids undesirable oscillations of the thermal protection circuit. The switch continues to cycle in this manner until the load fault is removed, resulting in a pulsed output. The FLG open-drain output is asserted when an overcurrent occurs with 7-ms dealitch.



Application Note (Continued)

Reverse Current Protection

In a normal MOSFET switch, current can flow in reverse direction (from the output side to the input side) when the output side voltage is higher than the input side, even when the switch is turned off. A reverse-current blocking feature is implemented in the AP21x1 series to prevent such back currents. This circuit is activated by the difference between the output voltage and the input voltage. When the switch is disabled, this feature blocks reverse current flow from the output back to the input.

Special Functions:

Discharge Function

When enable is de-asserted, the discharge function is active. The output capacitor is discharged through an internal NMOS that has a discharge resistance of 100Ω . Hence, the output voltage drops down to zero. The time taken for discharge is dependent on the RC time constant of the resistance and the output capacitor.

FLG Response

The FLG open-drain output goes active low for any of the two conditions: Over-Current or Over-Temperature. The time from when a fault condition is encountered to when the FLG output goes low is 7-ms (TYP). The FLG output remains low until both over-current and over-temperature conditions are removed. Connecting a heavy capacitive load to the output of the device can cause a momentary Over-current condition, which does not trigger the FLG due to the 7-ms deglitch timeout. The 7-ms timeout is also applicable for Over-current recovery and Thermal recovery. The AP2161D/AP2171D are designed to eliminate erroneous Over-current reporting without the need for external components, such as an RC delay network.

Applications Information:

Power Supply Considerations

A 0.01- μ F to 0.1- μ F X7R or X5R ceramic bypass capacitor between IN and GND, close to the device, is recommended. This limits the input voltage drop during line transients. Placing a high-value electrolytic capacitor on the input (10- μ F minimum) and output pin(s) is recommended when the output load is heavy. This precaution also reduces power-supply transients that

may cause ringing on the input. Additionally, bypassing the output with a 0.01- μ F to 0.1- μ F ceramic capacitor improves the immunity of the device to short-circuit transients. This capacitor also prevents output from going negative during turn-off due to inductive parasitics.

Power Dissipation and Junction Temperature

The low on-resistance of the internal MOSFET allows the small surface-mount packages to pass large current. Using the maximum operating ambient temperature (T_A) and $R_{DS(ON)}$, the power dissipation can be calculated by:

$$P_D = R_{DS(ON)} \times I^2$$

The junction temperature can be calculated by $T_J = P_D \; x \; R_{\theta JA} + T_A \label{eq:TJ}$

Where:

TA= Ambient temperature °C RθJA = Thermal resistance PD = Total power dissipation

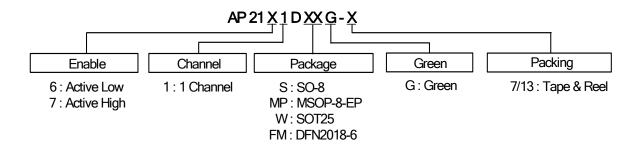
Generic Hot-Plug Applications

In many applications it may be necessary to remove modules or PC boards while the main unit is still operating. These are considered hot-plug applications. Such implementations require the control of current surges as seen by the main power supply and the card being inserted. The most effective way to control these surges is to limit and slowly ramp up the current and voltage being applied to the card, similar to the way in which a power supply normally turns on. Due to the controlled rise and fall times of the AP2161D/AP2171D, these devices can be used to provide a softer start-up to devices being hot-plugged into a powered system. The UVLO feature of the AP2161D/AP2171D also ensures that the switch is off after the card has been removed, and that the switch is off during the next insertion.

By placing the AP2161D/AP2171D between the $V_{\rm CC}$ input and the rest of the circuitry, the input power reaches these devices first after insertion. The typical rise time of the switch is approximately 1ms, providing a slow voltage ramp at the output of the device. This implementation controls the system surge current and provides a hot-plugging mechanism for any device.



Ordering Information

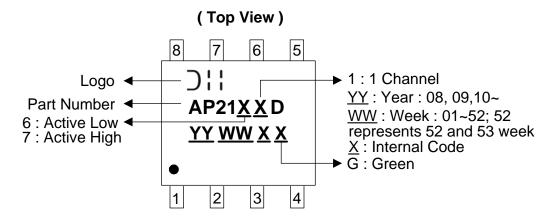


	Device	Package	Packaging	7"/13" Tape and Reel	
	Device	Code	(Note 6)	Quantity	Part Number Suffix
B ,	AP21X1DSG-13	S	SO-8	2500/Tape & Reel	-13
B	AP21X1DMPG-13	MP	MSOP-8EP	2500/Tape & Reel	-13
B ,	AP21X1DWG-7	W	SOT25	3000/Tape & Reel	-7
B ,	AP21X1DFMG-7	FM	U-DFN2018-6	3000/Tape & Reel	-7

Notes: 6. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

Marking Information

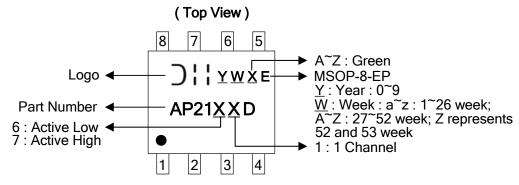
(1) SO-8





Marking Information (Continued)

(2) MSOP-8EP



(3) SOT25

(Top View)

5 4 <u>XX Y W X</u>
1 2 3

XX: Identification code

Y: Year 0~9

W: Week: A~Z: 1~26 week;

a~z: 27~52 week; z represents

52 and 53 week

X: A~Z: Green

Device	Package type	Identification Code
AP2161DW	SOT25	JC
AP2171DW	SOT25	JD

(4) U-DFN2018-6

(Top View)

 XX: Identification Code

Y: Year: 0~9

<u>W</u>: Week: A~Z: 1~26 week;

a~z: 27~52 week; z represents

52 and 53 week

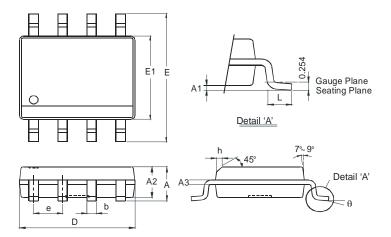
X: A~Z: Green

Device	Package type	Identification Code
AP2161DFM	U-DFN2018-6	JC
AP2171DFM	U-DFN2018-6	JD



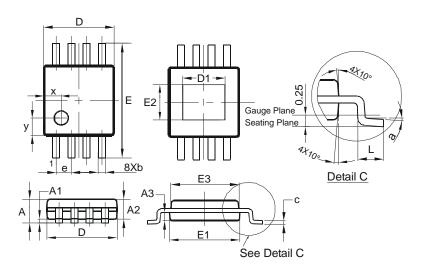
Package Outline Dimensions (All Dimensions in mm)

(1) SO-8



	SO-8					
Dim	Min	Max				
Α	-	1.75				
A1	0.10	0.20				
A2	1.30	1.50				
А3	0.15	0.25				
b	0.3	0.5				
D	4.85	4.95				
Е	5.90	6.10				
E1	3.85	3.95				
е	1.27	Тур				
h	-	0.35				
L	0.62	0.82				
θ	0°	8°				
All Di	mensions	in mm				

(2) MSOP-8-EP

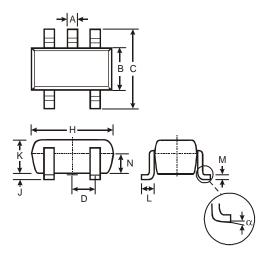


MSOP-8EP						
Dim	Min	Max	Тур			
Α	-	1.10	-			
A1	0.05	0.15	0.10			
A2	0.75	0.95	0.86			
A3	0.29	0.49	0.39			
b	0.22	0.38	0.30			
C	0.08	0.23	0.15			
D	2.90	3.10	3.00			
D1	1.60	2.00	1.80			
Е	4.70	5.10	4.90			
E1	2.90	3.10	3.00			
E2	1.30	1.70	1.50			
E3	2.85	3.05	2.95			
е	-	-	0.65			
١	0.40	0.80	0.60			
а	0°	8°	4°			
х	-	-	0.750			
у	-	-	0.750			
All C	<u> </u>					



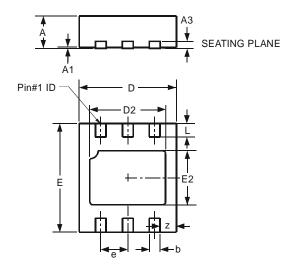
Package Outline Dimensions (Continued)

(3) SOT25



	SOT25					
Dim	Min	Max	Тур			
Α	0.35	0.50	0.38			
В	1.50	1.70	1.60			
С	2.70	3.00	2.80			
D	_	_	0.95			
Н	2.90	3.10	3.00			
J	0.013	0.10	0.05			
K	1.00	1.30	1.10			
L	0.35	0.55	0.40			
M	0.10	0.20	0.15			
N	0.70	0.80	0.75			
α	0°	8°	_			
All D	imensi	ons in	mm			

(4) U-DFN2018-6

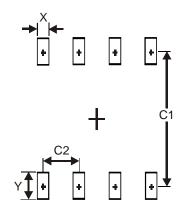


U-DFN2018-6				
Dim	Min	Max	Тур	
Α	0.545	0.605	0.575	
A1	0	0.05	0.02	
А3			0.13	
b	0.15	0.25	0.20	
D	1.750	1.875	1.80	
D2	1.30	1.50	1.40	
е	_	_	0.50	
E	1.95	2.075	2.00	
E2	0.90	1.10	1.00	
١	0.20	0.30	0.25	
Z	_	_	0.30	
All Dimensions in mm				



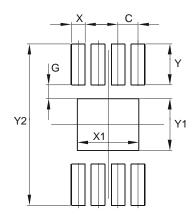
Suggested Pad Layout (All Dimensions in mm)

(1) SO-8



Dimensions	Value (in mm)
Х	0.60
Υ	1.55
C1	5.4
C2	1.27

(2) MSOP-8-EP

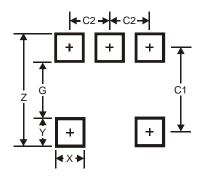


Dimensions	Value (in mm)
С	0.650
G	0.450
X	0.450
X1	2.000
Y	1.350
Y1	1.700
Y2	5.300



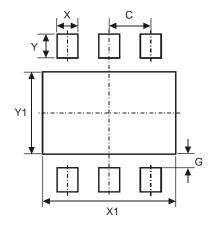
Suggested Pad Layout (Continued)

(3) SOT25



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95

(4) U-DFN2018-6

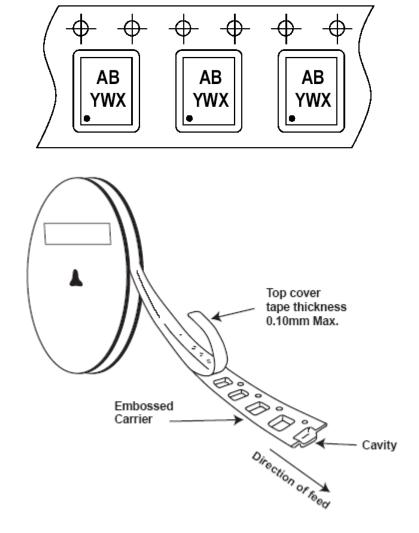


Dimensions	Value (in mm)
С	0.50
G	0.20
Х	0.25
X1	1.60
Y	0.35
V1	1.20



Taping Orientation (Note 7)

For DFN2018-6



Notes: 7. The taping orientation of the other package type can be found on our website at http://www.diodes.com/datasheets/ap02007.pdf



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